

ABSTRACT OF THE DISCLOSURE

A method of wire bonding of a semiconductor device for resolving oxidation of copper bonding pad is disclosed. The method comprises the steps of exposing the copper bonding pad of a wafer which has been completed with semiconductor circuit fabrication; covering the copper bonding pad of the wafer with a protective anti-oxidization film which will be vaporized when heated; performing wire bonding directly without requiring the removal of the protective film, employing ultrasonic vibration energy, pressurizing deformation energy and heat energy in the course of bonding to vaporize the protective film so that the metal wire and the copper pad form a large area intermetallic compound layer for bonding.